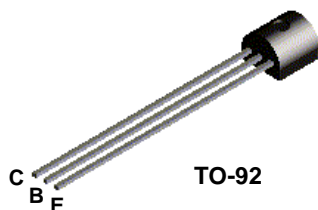
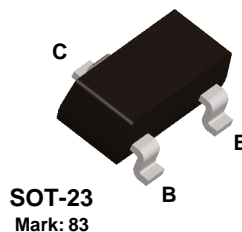


2N4400



MMBT4400



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CB0}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	1.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4400	*MMBT4400	
P _D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	357	°C/W

NPN General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \mu\text{A}, I_C = 0$	6.0		V
I_{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μA
I_{BL}	Emitter Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 150 \text{ mA}$ $V_{CE} = 2.0 \text{ V}, I_C = 500 \text{ mA}$	20 40 50 20	150	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.40 0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	0.95 1.2	V

SMALL SIGNAL CHARACTERISTICS

C_{ob}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$		6.5	pF
C_{ib}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$		30	pF
h_{fe}	Small-Signal Current Gain	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	2.0		
h_{fe}	Small-Signal Current Gain	$V_{CE} = 10 \text{ V}, I_C = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$	20	250	
h_{ie}	Input Impedance	$f = 1.0 \text{ kHz}$	0.5	7.5	$\text{K}\Omega$
h_{re}	Voltage Feedback Ratio		0.1	8.0	$\times 10^{-4}$
h_{oe}	Output Admittance		1.0	30	μmhos

SWITCHING CHARACTERISTICS

t_d	Delay Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA},$		15	ns
t_r	Rise Time	$I_{B1} = 15 \text{ mA}, V_{BE(off)} = 0.0 \text{ V}$		20	ns
t_s	Storage Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$		225	ns
t_f	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		30	ns

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

2N4400 / MMBT4400